

NTS110P03P3



P-Channel Enhancement Mode Trench Power MOSFET

Voltage: -30 Volts

Current: -40 Ampers

Package: PDFN3*3

Features

- NH'S Advanced Trench Technology
- Low Rds(on) For Low On-State Loss
- High EAS For High Reliability
- Excellent Qg*Rds(on) Product(FOM)

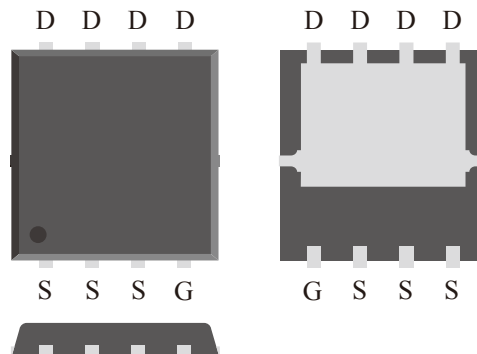
Typical Applications

- DC-DC Converter
- Battery Management System(BMS)
- Printed Circuit Board For Control Circuit
- Uninterruptible Power Supplies(UPS)

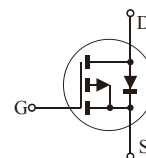
Product Summary

VDS Min.@Tj	-30	V
Id Min.@Ta	-40	A
RDS(ON)(TYP)@-10V	11	mΩ

Diagram:



Polarity:



***100% UIS TESTED**

***100% ΔVDS TESTED**

Absolute Maximum Ratings (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Ratings	Unit
Drain-Source Voltage		V _{DS}	-30	V
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current (Note 1)	Ta= 25 °C	I _D	-40	A
	Ta= 100 °C		-26	
Drain Current-Pulse (Note 1)	Tj< 150 °C	I _{DM}	-160	A
Maximum Power Dissipation Power Dissipation Derating Factor Above 25°C	Ta= 25 °C	P _D	34	W
	Ta= 100 °C		14	
Derating Factor		D _F	0.27	W/°C
Avalanche Current,Single Pulse (Note 1)	L= 0.5 mH	I _{AS}	-20	A
Single Pulse Avalanche Energy (Note 1) Test Circuit & Waveform See Fig.17	L= 0.5 mH IAS= -20 A, RG= 10.0 Ω Starting Tj=25 °C, VG = -10 V	E _{AS}	100	mJ

Thermal Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Typ.	Unit
Junction Temperature		T _J	-55 to 150	°C
Storage Temperature Range		T _{STD}	-55 to 150	°C
Thermal Resistance Junction To Ambient With Steady-State	Still Air Environment With Ta=25 °C	R _{θJA}	62	°C/W
Thermal Resistance Junction-Case With Steady-State	Device Mounted On 1 in2 FR-4 Board With 2oz. Copper	R _{θJC}	3.7	

Notes: 1.Pulse Width Limited By Max. Junction Temperature. (See Fig. 14).

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Electrical Characteristics (Ta=25°C Unless Otherwise Specified)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Static Off Characteristics						
Drain-Source Breakdown Voltage	VGS=0V,ID=-250uA	BV _{DSS}	-30	--	--	V
Bvdss Temperature Coefficient	ID=-250uA,Reference25℃	ΔBV _{DSS} /ΔT _J	--	0.03	--	V/℃
Drain-Source Leakage Current	VDS= -30 V,VGS=0V	I _{DSS}	--	--	-1	uA
Gate-Body Leakage Current	VGS= ±20 V,VDS=0V	I _{GSS}	--	--	±100	nA
Forward Transconductance	ID= -20.0 A,VDS= -5 V	g _{fs}	--	14	--	S
Static On Characteristics						
Gate Threshold Voltage	VGS= VDS ID=-250uA	V _{GS(TH)}	-1.2	-1.6	-2	V
Drain-Source On Resistance	ID= -20.0 A,VGS= -10 V	R _{DS(ON)}	--	11	14	mΩ
	ID= -20.0 A,VGS= -5 V		--	15	20	
Dynamic Characteristics						
Input Capacitance	VDS= -15 V	C _{iss}	--	1470	--	pF
Output Capacitance	VGS= 0 V	C _{oss}	--	165	--	pF
Reverse Transfer Capacitance	F= 1 MHZ	C _{rss}	--	130	--	pF
Gate Resistance	VGS=0V,VDS=0V, Freq.=1MHz	R _g	--	13	--	Ω
Switching Paramters (Test Circuit & Waveform See Fig.15)						
Turn-On Delay Time	VDS= -15 V	t _{d(on)}	--	14.5	--	ns
Turn-On Rise Time	VGS= -10.0 V	t _r	--	3	--	ns
Turn-Off Delay Time	RG= 10.0 Ω	t _{d(off)}	--	91	--	ns
Turn-Off Rise Time		t _f	--	35	--	ns
Gate Charge Paramters (Test Circuit & Waveform See Fig.16)						
Total Gate Charge	VDS= -15 V	Q _g	--	38	--	nC
Gate-Source Charge	VGS= -10.0 V	Q _{gs}	--	8	--	nC
Gate-Drain Charge	ID= -20.0 A	Q _{gd}	--	9	--	nC
Drain-Source Diode Characteristics And Maximum Ratings (Test Circuit & Waveform See Fig.18)						
Max. Diode Forward Cuurent		I _S	--	--	-40.0	A
Max. Pulsed Forward Cuurent		I _{SM}	--	--	-160	A
Diode Forward Voltage	ID= -20.0 A,VGS=0V	V _{SD}	--	-0.84	-1.2	V
Reverse Recovery Time	IS= -20.0 A,di/dt= -100 A/us	t _{rr}	--	14	--	ns
Reverse Recovery Charge	VGS= 0.0 V	Q _{rr}	--	5	--	nC
Reverse Recovery Current		I _{RRM}	--	-1.0	--	A

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Typical Characteristics Curves

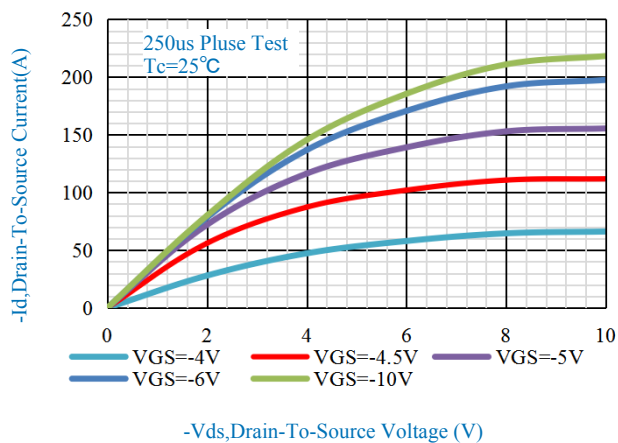


Fig.1-Output Characteristics

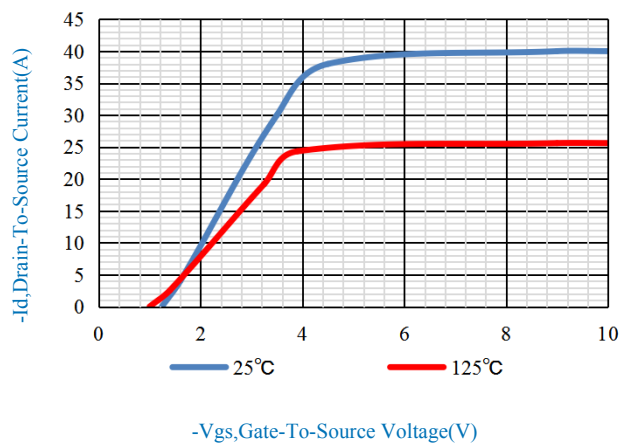


Fig.2-Transfer Characteristics

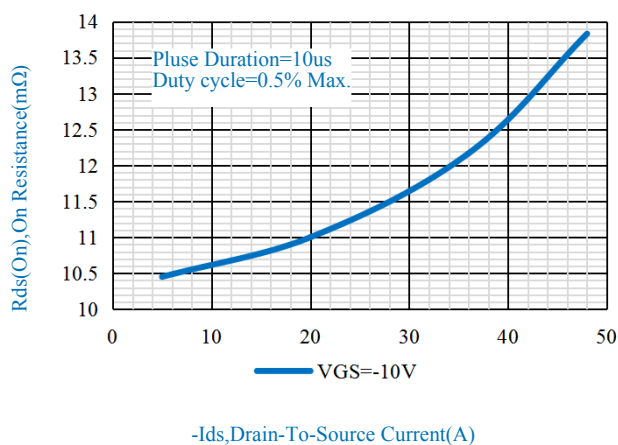


Fig.3-On Resistance Vs. Drain Current

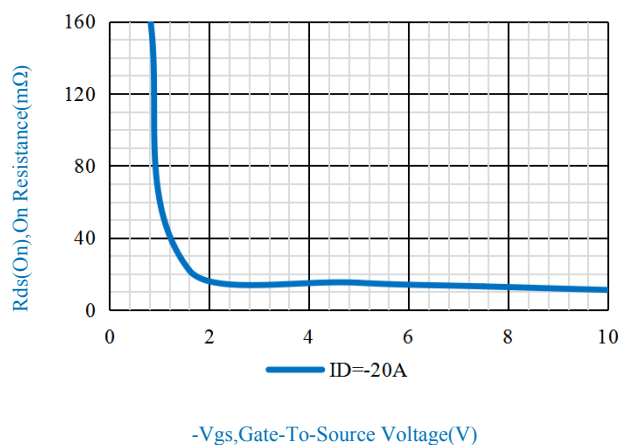


Fig.4-On Resistance Vs. Gate Source Voltage

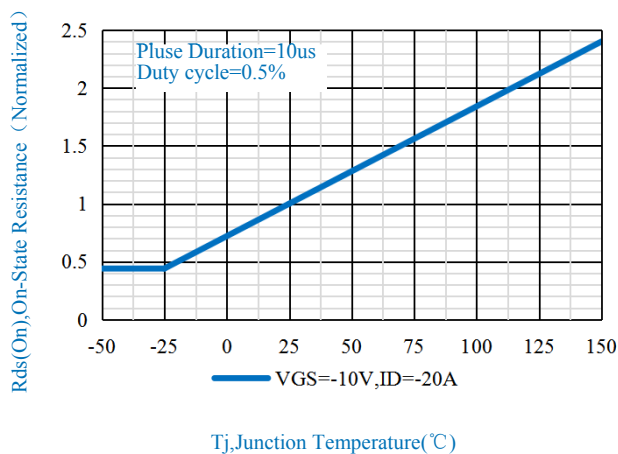


Fig.5-On Resistance Vs. Junction Temperature

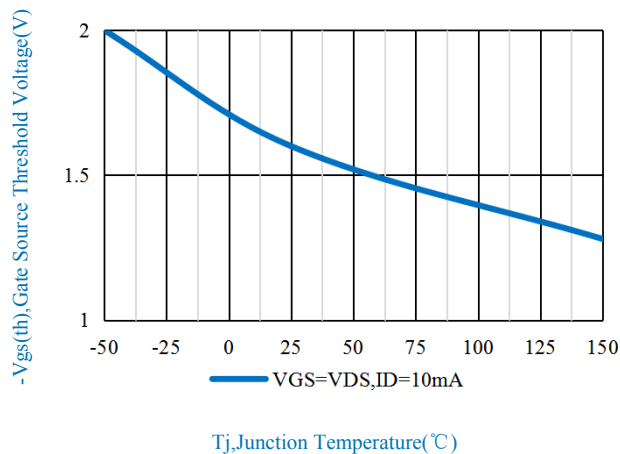


Fig.6-Gate Source Threshold Voltage Vs. Junction Temperature

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Typical Characteristics Curves

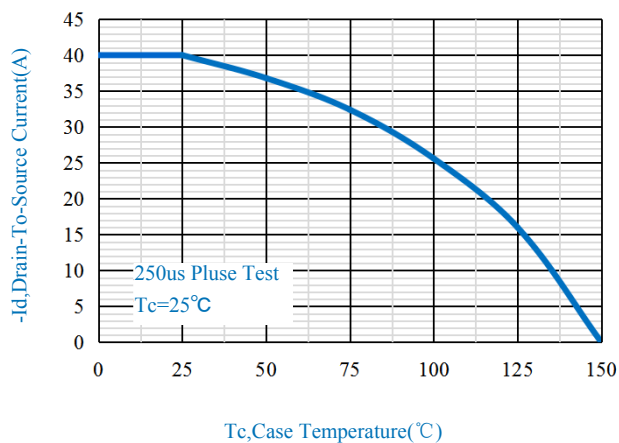


Fig.7-Maximum Continuous Drain Current Vs. Case Temperature

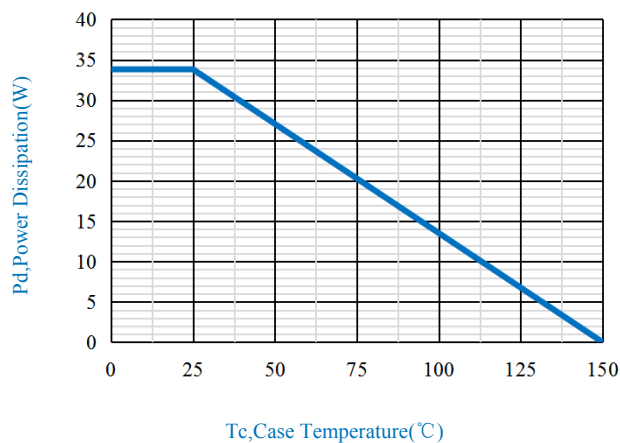


Fig.8-Maximum Power Dissipation Vs. Case Temperature

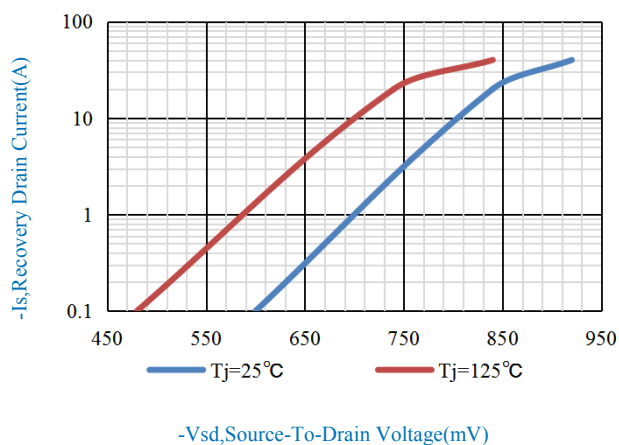


Fig.9-Source-To-Drain Diode Forward Voltage

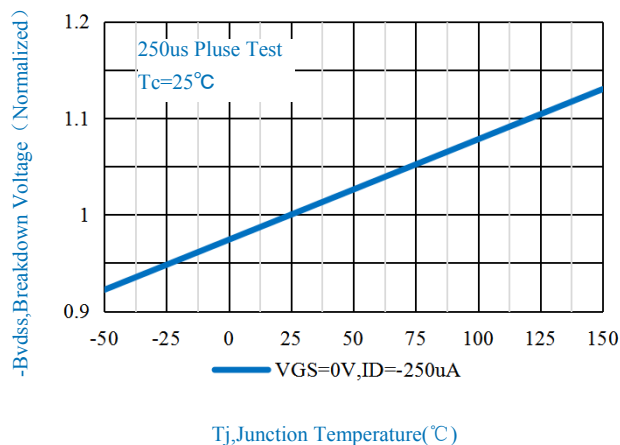


Fig.10-Breakdown Voltage Vs. Junction Temperature

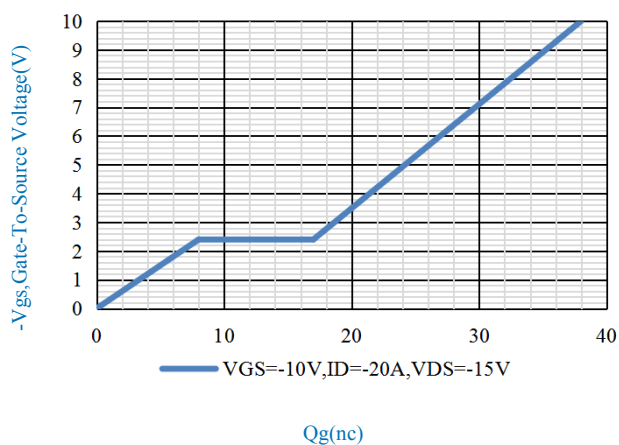


Fig.11-Gate Charge Waveform

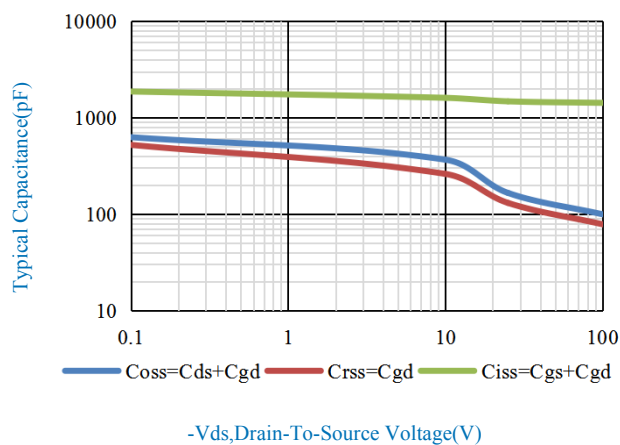


Fig.12-Typical Capacitance Vs. Drain-To-Source Voltage

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Typical Characteristics Curves

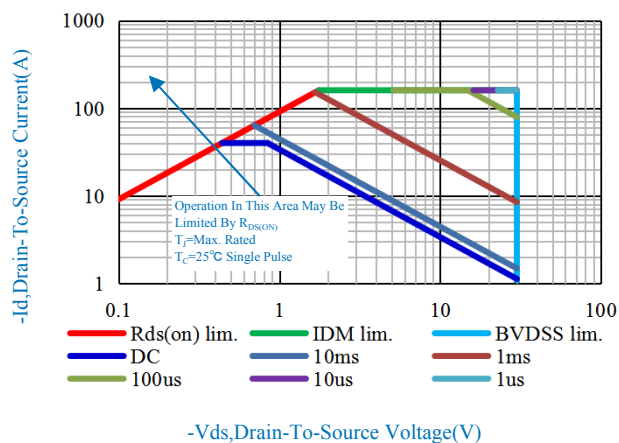


Fig.13-Maximum Safe Operating Area(SOA)

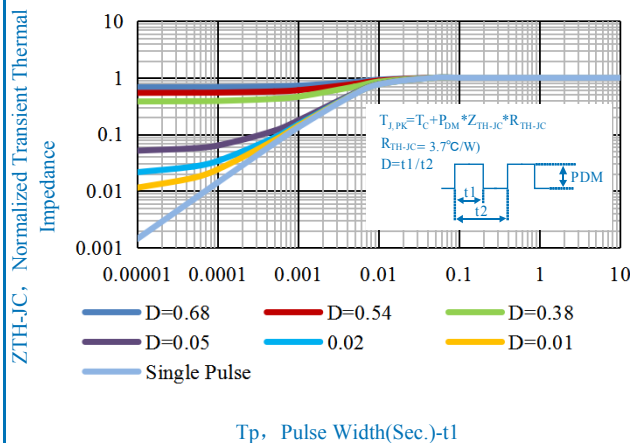


Fig.14- Normalized Maximum Transient Thermal Impedance Vs. Pulse Width

Test Circuit & Waveform

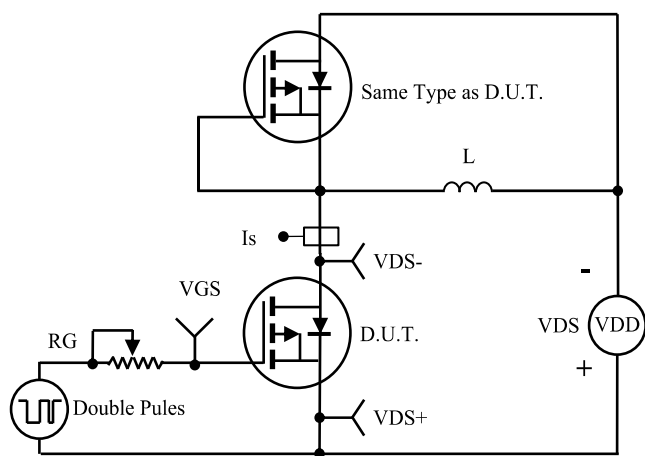


Fig.15- Resistive Switching Test Circuit & Waveform

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Test Circuit & Waveform

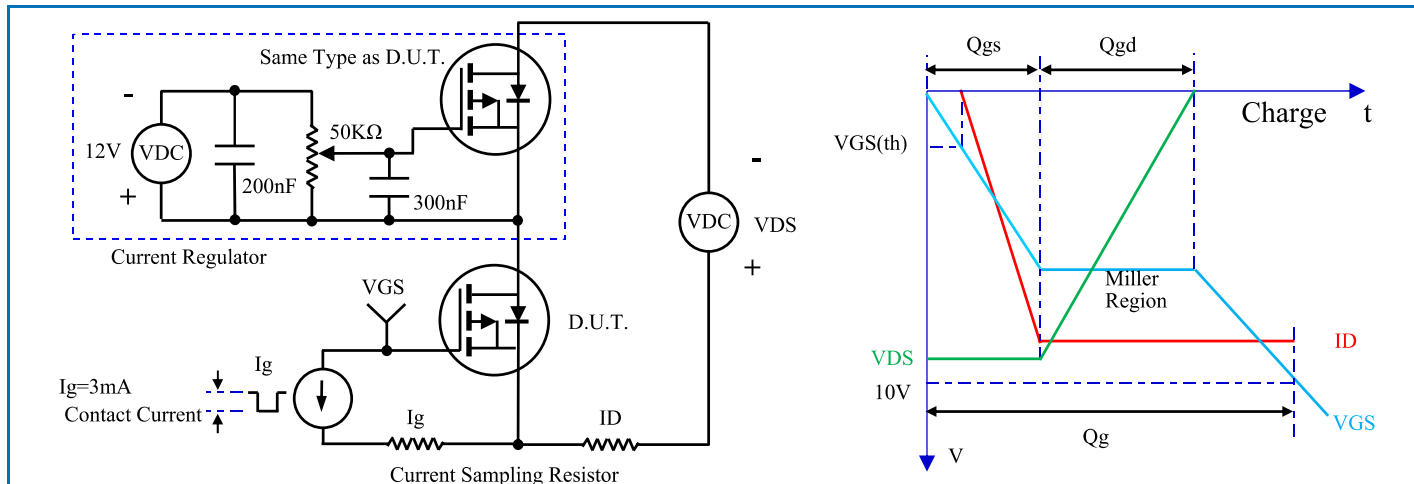


Fig.16-Gate Charge Test Circuit & Waveform

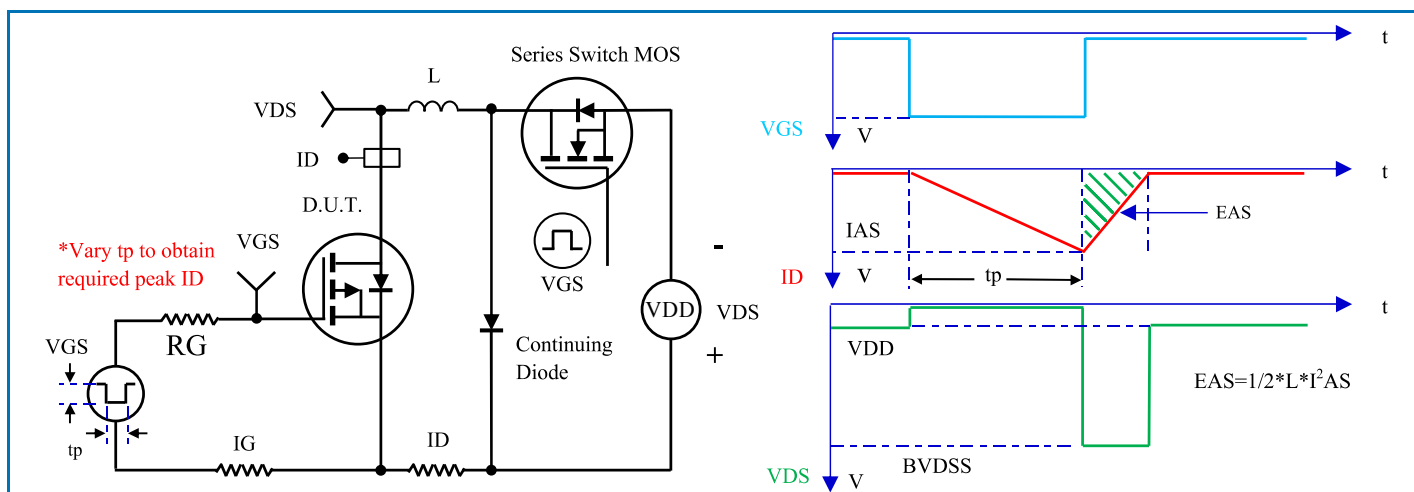


Fig.17- Unclamped Inductive Switching (UIS) Test Circuit & Waveform

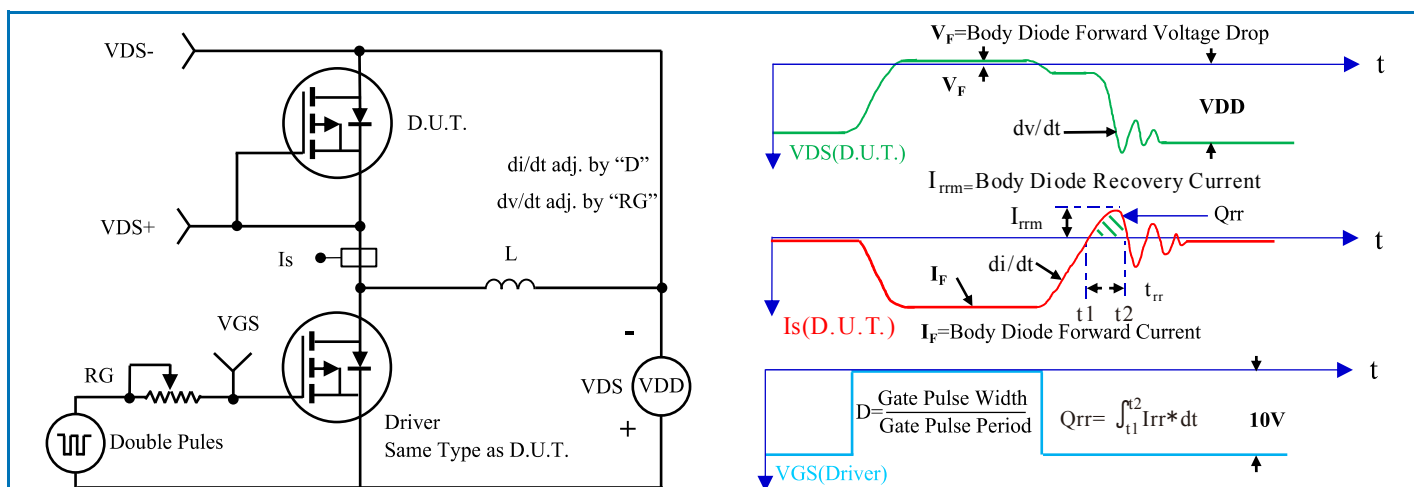


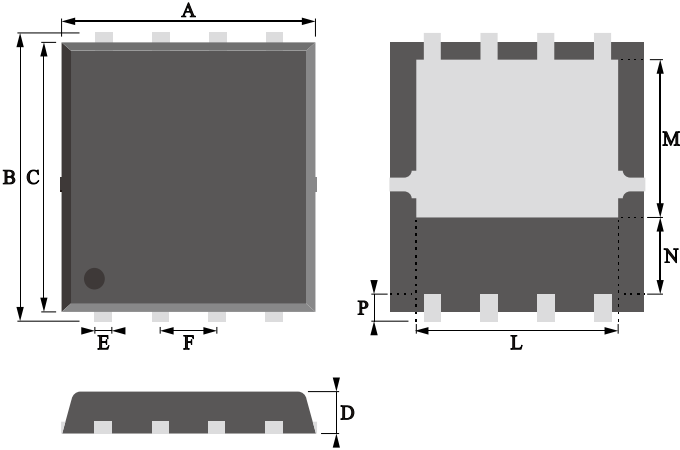
Fig.18- Diode Recovery Test Circuit & Waveform

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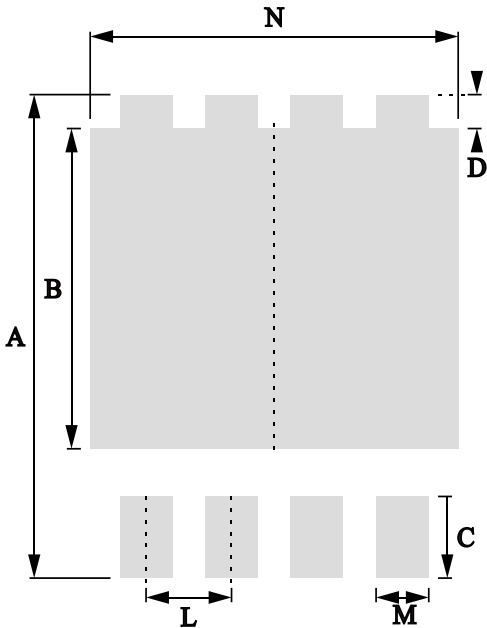
OUTLINE DRAWINGS



PDFN3*3

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.80	-	3.60	0.1102	-	0.1417
B	2.70	-	3.50	0.1063	-	0.1378
C	3.00	-	3.80	0.1181	-	0.1496
D	0.55	-	1.05	0.0217	-	0.0413
E	0.15	-	0.45	0.0059	-	0.0177
F	0.40	0.65	0.90	0.0157	-	0.0354
M	1.50	-	2.10	0.0591	-	0.0827
L	2.30	-	2.90	0.0906	-	0.1142
N	0.45	-	0.95	0.0177	-	0.0374
P	0.20	-	0.60	0.0079	-	0.0236

RECOMMEDND LAYOUT DRAWINGS



PDFN3*3

OUTLINE DIMENSIONS						
Dim.	Milimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	-	3.55	-	-	0.1398	-
B	-	2.35	-	-	0.0925	-
C	-	0.60	-	-	0.0236	-
D	-	0.25	-	-	0.0098	-
L	-	0.65	-	-	0.0256	-
M	-	0.40	-	-	0.0157	-
N	-	2.80	-	-	0.1102	-

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MARKING INFORMATION



MARKING INSTRUCTIONS

NH=Niuhan Trademark
FF=Product Line Code,According To Actual Changes
YWW=Date Code,According To Actual Changes
LLWWF=Internal Code,According To Actual Changes
NTS110P03P3=Model

PACKING INFORMATION

Package Type	Package Code	Product Weight Approx(g/Pcs)	Package Method	Quantity (Pcs/Min. Pack.)	Quantity (Pcs/Inner Box)	Quantity (Pcs/Carton)
PDFN3*3	P1	0.0198	13" Reel	5000	10000	50000

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Recommended wave soldering condition

Product	Peak Temperature	Soldering Time
Pb-free devices	260 +0/-5 °C	5 +1/-1 seconds

Recommended temperature profile for IR reflow

	Profile feature	Sn-Pb eutectic Assembly	Pb-free Assembly
	Average ramp-up rate (T _{smax} to T _p)	3°C/second max.	3°C/second max.
	Preheat-Temperature Min (T _S min) -Temperature Max (T _S max) -Time(t _s min to t _s max)	100°C 150°C 60-120 seconds	150°C 200°C 60-180 seconds
	Time maintained above: -Temperature (T _L) - Time (t _L)	183°C 60-150 seconds	217°C 60-150 seconds
	Peak Temperature(T _P)	240 +0/-5 °C	260 +0/-5 °C
	Time within 5°C of actual peak temperature (t _p)	10-30 seconds	20-40 seconds
	Ramp down rate	6°C/second max.	6°C/second max.
	Time 25 °C to peak temperature	6 minutes max.	8 minutes max.

Note : All temperatures refer to topside of the package, measured on the package body surface.

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Specification Revision History

Rev.	Date	Changed Items	Pre-Changed Content	Changed Content
A/1	2014-10-20	First Issue		
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